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Kind regards,

Team Nexperia

# PDTD123T series

NPN 500 mA, 50 V resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

Rev. 03 — 16 November 2009

Product data sheet

## 1. Product profile

## 1.1 General description

500 mA NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package	Package		
	NXP	JEITA	JEDEC	_
PDTD123TK	SOT346	SC-59A	TO-236	PDTB123TK
PDTD123TS[1]	SOT54	SC-43A	TO-92	PDTB123TS
PDTD123TT	SOT23	-	TO-236AB	PDTB123TT

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2).

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

- Cost saving alternative for BC817 series in digital applications
- Switching loads

## 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{CEO}}$	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current		-	-	500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



### **Pinning information** 2.

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	1 1 2 3 001aab347	1 R1 3
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab348	1 R1 3
SOT54 va	ariant		
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab447	1 R1 3
SOT23, S	OT346		
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)	1 2 006aaa144	1 R1 2 sym012

### **Ordering information** 3.

Table 4. **Ordering information** 

Type number	Package					
	Name	Description	Version			
PDTD123TK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTD123TS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTD123TT	-	plastic surface mounted package; 3 leads	SOT23			

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

### **Marking** 4.

Table 5. **Marking codes** 

Type number	Marking code <sup>[1]</sup>
PDTD123TK	E9
PDTD123TS	TD123TS
PDTD123TT	*1T

<sup>[1] \* = -:</sup> made in Hong Kong

### **Limiting values** 5.

Table 6. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
VI	input voltage				
	positive		-	+12	V
	negative		-	<b>-</b> 5	V
I <sub>O</sub>	output current		-	500	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25~^{\circ}C$	[1]		
	SOT346		-	250	mW
	SOT54		-	500	mW
	SOT23		-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

#### Thermal characteristics 6.

**Thermal characteristics** Table 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT346		-	-	500	K/W
	SOT54		-	-	250	K/W
	SOT23		-	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### **Characteristics** 7.

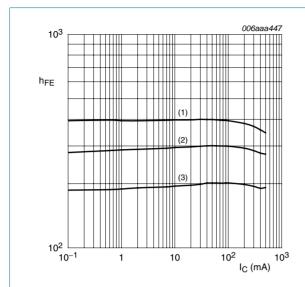
**Characteristics** Table 8.

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off	$V_{CB} = 40 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; I_{B} = 0 \text{ A}$	-	-	0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	100	300	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}$	-	-	0.3	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	7	-	pF

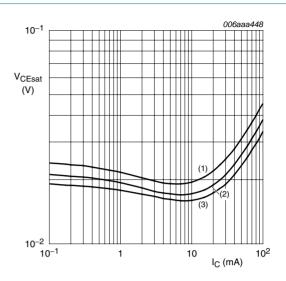
# PDTD123T series

NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open



- $V_{CE} = 5 V$
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

DC current gain as a function of collector Fig 1. current; typical values

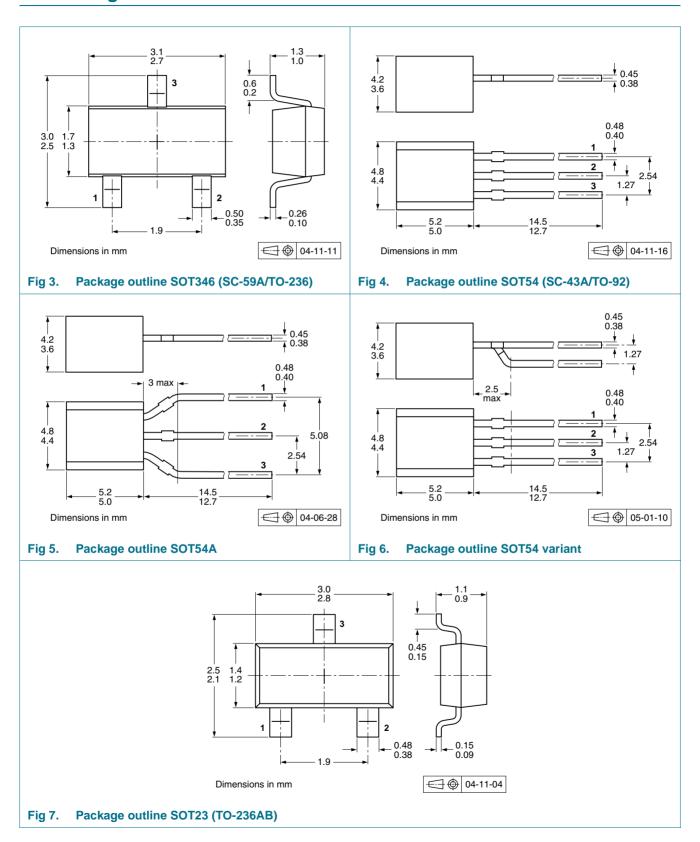


- $I_{\rm C}/I_{\rm B} = 20$
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

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## 8. Package outline



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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

## **Packing information**

Table 9. **Packing methods** 

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity	
			3000	5000	10000
PDTD123TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTD123TS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTD123TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235

<sup>[1]</sup> For further information and the availability of packing methods, see Section 12.



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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

## 10. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTD123T_SER_3	20091116	Product data sheet	-	PDTD123T_SER_2	
Modifications:	<ul> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technica content</li> </ul>				
PDTD123T_SER_2	20050721	Product data sheet	-	PDTD123T_SER_1	
PDTD123T_SER_1	20050603	Product data sheet	-	-	

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PDTD123T series

## NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

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